

UMC2NT1, UMC3NT1, UMC5NT1

Preferred Devices

Dual Common Base-Collector Bias Resistor Transistors

NPN and PNP Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the UMC2NT1 series, two complementary BRT devices are housed in the SOT-353 package which is ideal for low power surface mount applications where board space is at a premium.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Available in 8 mm, 7 inch/3000 Unit Tape and Reel
- Pb-Free Packages are Available

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted, common for Q_1 and Q_2 , – minus sign for Q_1 (PNP) omitted)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current	I_C	100	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

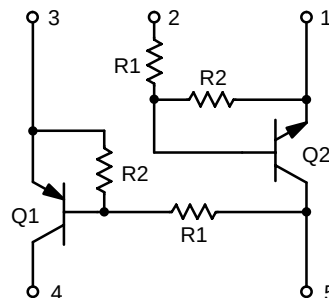
Thermal Resistance – Junction-to-Ambient (surface mounted)	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Total Package Dissipation @ $T_A = 25^\circ\text{C}$ (Note 1)	P_D	150	mW

1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.



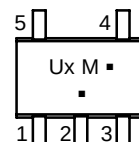
ON Semiconductor®

<http://onsemi.com>



SC-88A/SOT-353
CASE 419A
STYLE 6

MARKING DIAGRAM



Ux = Device Marking
x = 2, 3 or 5
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

UMC2NT1, UMC3NT1, UMC5NT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

Q1 TRANSISTOR: PNP

OFF CHARACTERISTICS

Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}$, $I_E = 0$)	I_{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current ($V_{CB} = 50\text{ V}$, $I_B = 0$)	I_{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0$, $I_C = 0\text{ mA}$)	I_{EBO}	–	–	0.2	mAdc
		–	–	0.5	
		–	–	1.0	

ON CHARACTERISTICS

Collector-Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	50	–	–	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 2.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	50	–	–	Vdc
DC Current Gain ($V_{CE} = 10\text{ V}$, $I_C = 5.0\text{ mA}$)	h_{FE}	60	100	–	
		35	60	–	
		20	35	–	
Collector-Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 0.3\text{ mA}$)	$V_{CE(SAT)}$	–	–	0.25	Vdc
Output Voltage (on) ($V_{CC} = 5.0\text{ V}$, $V_B = 2.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$)	V_{OL}	–	–	0.2	Vdc
Output Voltage (off) ($V_{CC} = 5.0\text{ V}$, $V_B = 0.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$)	V_{OH}	4.9	–	–	Vdc
Input Resistor	R_1	15.4	22	28.6	$\text{k}\Omega$
		7.0	10	13	
		3.3	4.7	6.1	
Resistor Ratio	R_1/R_2	0.8	1.0	1.2	
		0.8	1.0	1.2	
		0.38	0.47	0.56	

Q2 TRANSISTOR: NPN

OFF CHARACTERISTICS

Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}$, $I_E = 0$)	I_{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current ($V_{CB} = 50\text{ V}$, $I_B = 0$)	I_{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0$, $I_C = 0\text{ mA}$)	I_{EBO}	–	–	0.2	mAdc
		–	–	0.5	
		–	–	0.1	

ON CHARACTERISTICS

Collector-Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	50	–	–	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 2.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	50	–	–	Vdc
DC Current Gain ($V_{CE} = 10\text{ V}$, $I_C = 5.0\text{ mA}$)	h_{FE}	60	100	–	
		35	60	–	
		80	140	–	
Collector-Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 0.3\text{ mA}$)	$V_{CE(SAT)}$	–	–	0.25	Vdc
Output Voltage (on) ($V_{CC} = 5.0\text{ V}$, $V_B = 2.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$)	V_{OL}	–	–	0.2	Vdc
Output Voltage (off) ($V_{CC} = 5.0\text{ V}$, $V_B = 0.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$)	V_{OH}	4.9	–	–	Vdc
Input Resistor	R_1	15.4	22	28.6	$\text{k}\Omega$
		7.0	10	13	
		33	47	61	
Resistor Ratio	R_1/R_2	0.8	1.0	1.2	
		0.8	1.0	1.2	
		0.8	1.0	1.2	

UMC2NT1, UMC3NT1, UMC5NT1

ORDERING INFORMATION

Device	Package	Shipping [†]
UMC2NT1	SC-88A/SOT-353	3000 / Tape & Reel
UMC2NT1G	SC-88A/SOT-353 (Pb-Free)	3000 / Tape & Reel
UMC3NT1	SC-88A/SOT-353	3000 / Tape & Reel
UMC3NT1G	SC-88A/SOT-353 (Pb-Free)	3000 / Tape & Reel
UMC3NT2	SC-88A/SOT-353	3000 / Tape & Reel
UMC3NT2G	SC-88A/SOT-353 (Pb-Free)	3000 / Tape & Reel
UMC5NT1	SC-88A/SOT-353	3000 / Tape & Reel
UMC5NT1G	SC-88A/SOT-353 (Pb-Free)	3000 / Tape & Reel
UMC5NT2	SC-88A/SOT-353	3000 / Tape & Reel
UMC5NT2G	SC-88A/SOT-353 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Transistor 1 – PNP		Transistor 2 – NPN	
		R1 (K)	R2 (K)	R1 (K)	R2 (K)
UMC2NT1, G	U2	22	22	22	22
UMC3NT1, G	U3	10	10	10	10
UMC3NT2, G	U3	10	10	10	10
UMC5NT1, G	U5	4.7	10	47	47
UMC5NT2, G	U5	4.7	10	47	47

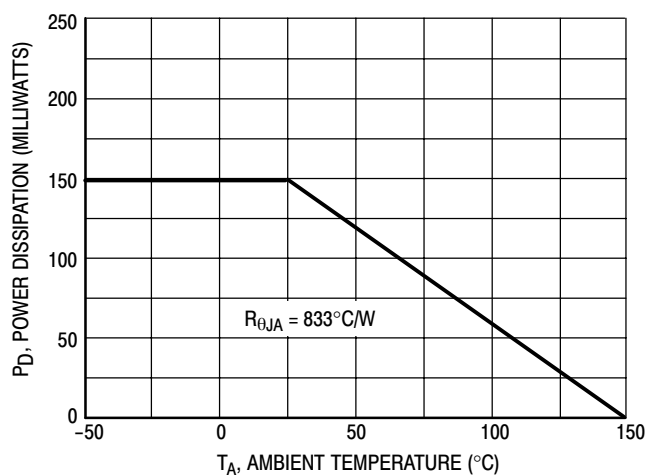


Figure 1. Derating Curve

UMC2NT1, UMC3NT1, UMC5NT1

TYPICAL ELECTRICAL CHARACTERISTICS — UMC2NT1 PNP TRANSISTOR

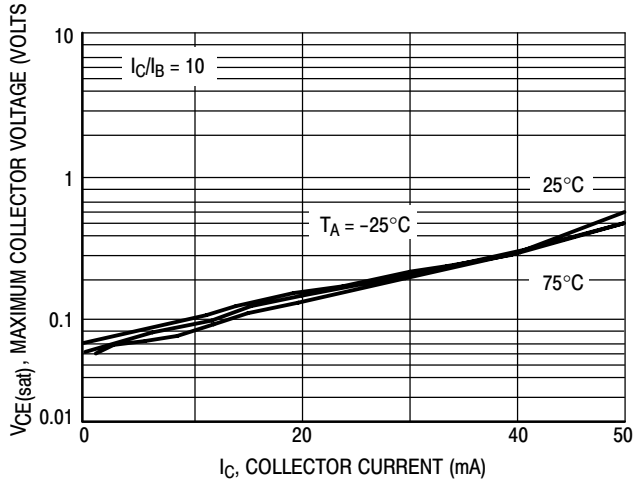


Figure 2. $V_{CE(sat)}$ versus I_C

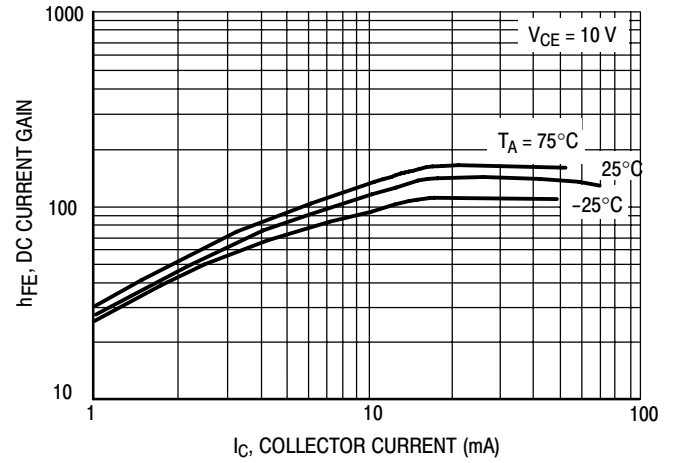


Figure 3. DC Current Gain

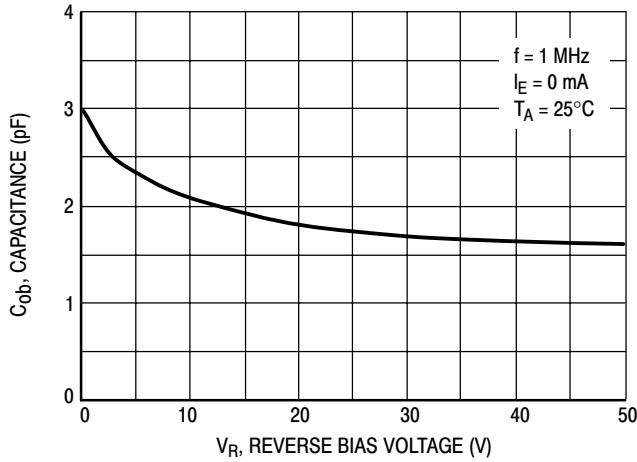


Figure 4. Output Capacitance

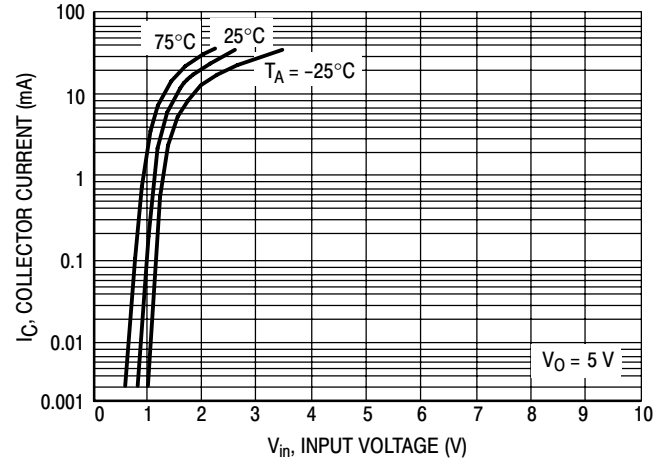


Figure 5. Output Current versus Input Voltage

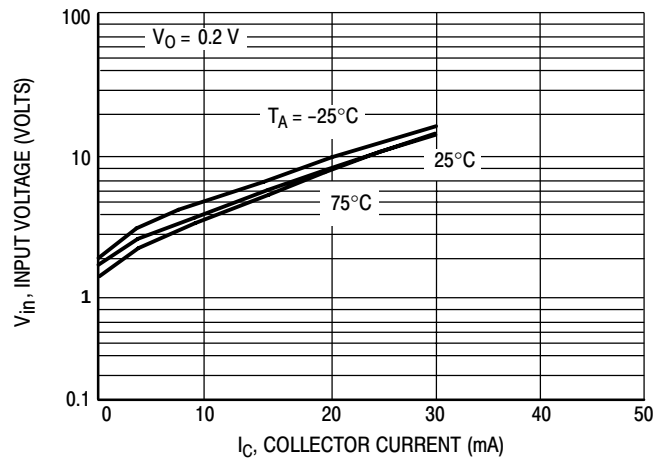


Figure 6. Input Voltage versus Output Current

UMC2NT1, UMC3NT1, UMC5NT1

TYPICAL ELECTRICAL CHARACTERISTICS — UMC2NT1 NPN TRANSISTOR

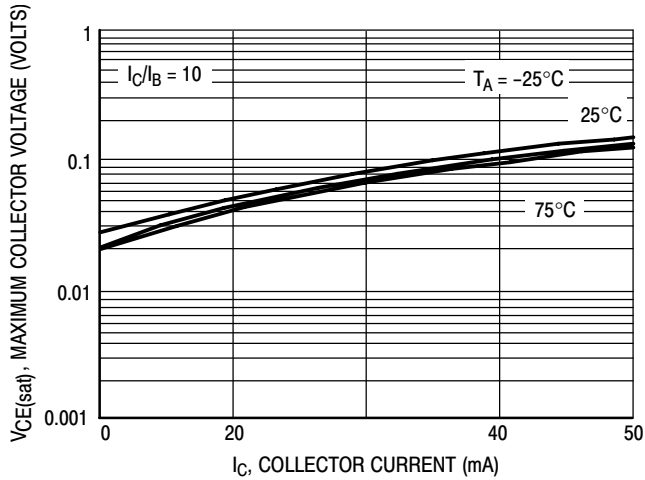


Figure 7. $V_{CE(sat)}$ versus I_C

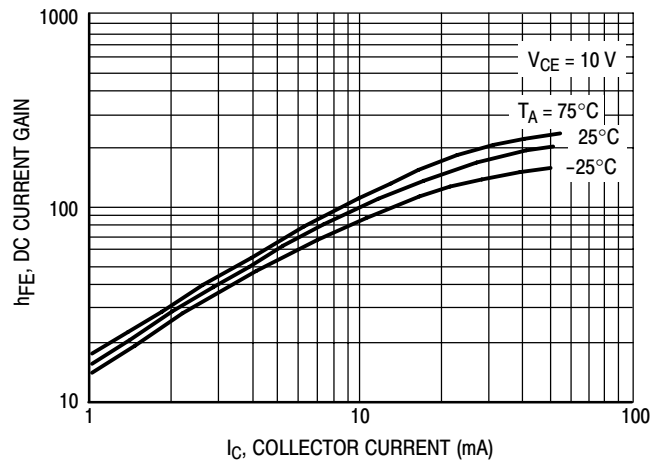


Figure 8. DC Current Gain

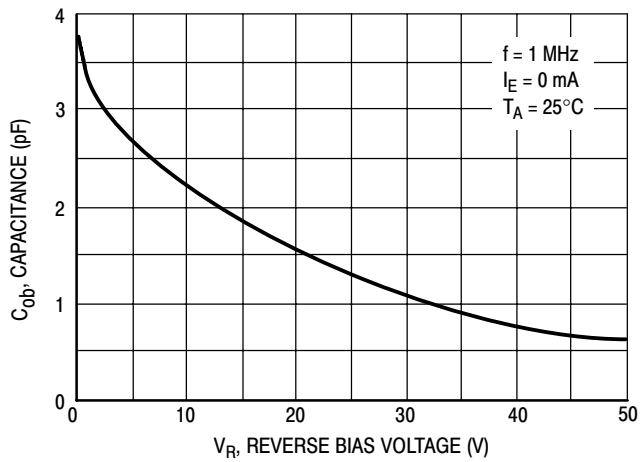


Figure 9. Output Capacitance

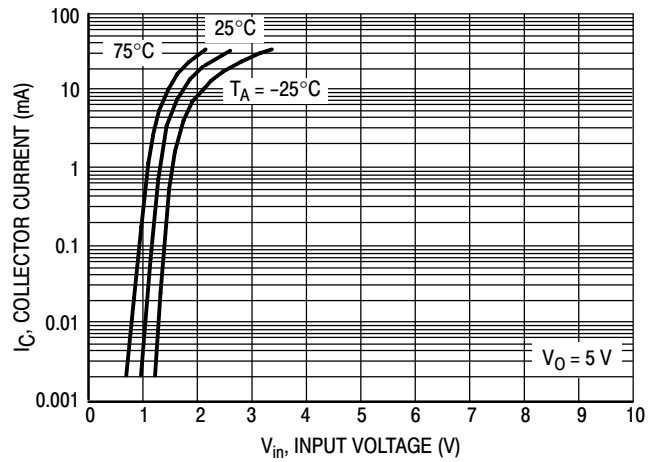


Figure 10. Output Current versus Input Voltage

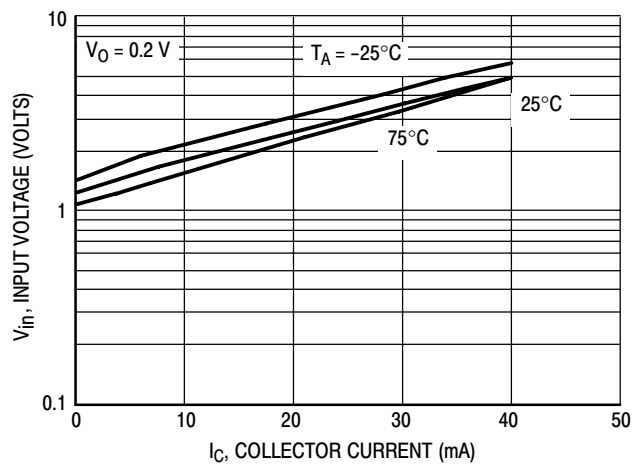


Figure 11. Input Voltage versus Output Current

UMC2NT1, UMC3NT1, UMC5NT1

TYPICAL ELECTRICAL CHARACTERISTICS — UMC3NT1 PNP TRANSISTOR

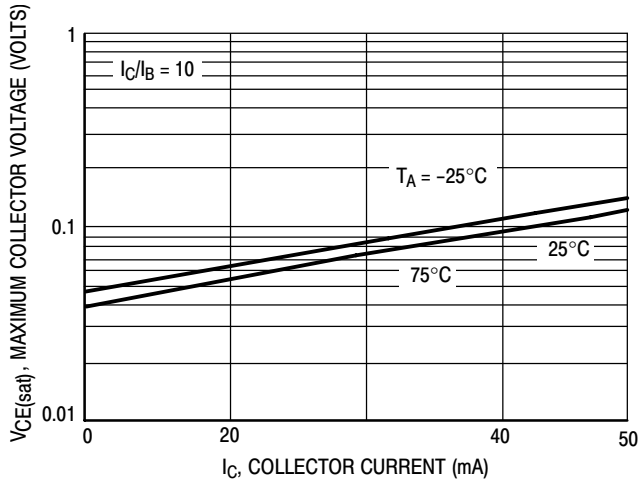


Figure 12. $V_{CE(sat)}$ versus I_C

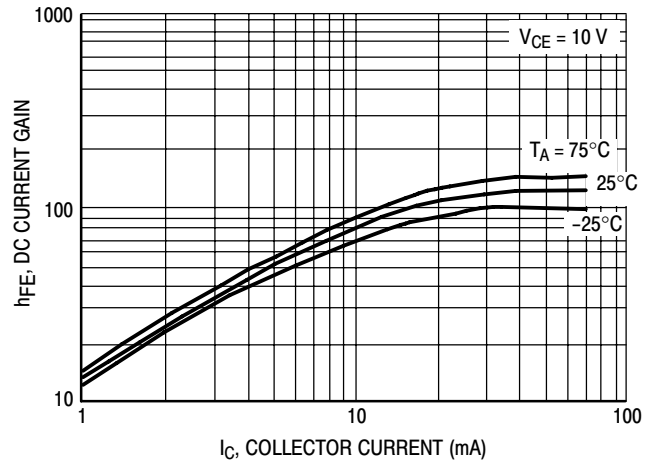


Figure 13. DC Current Gain

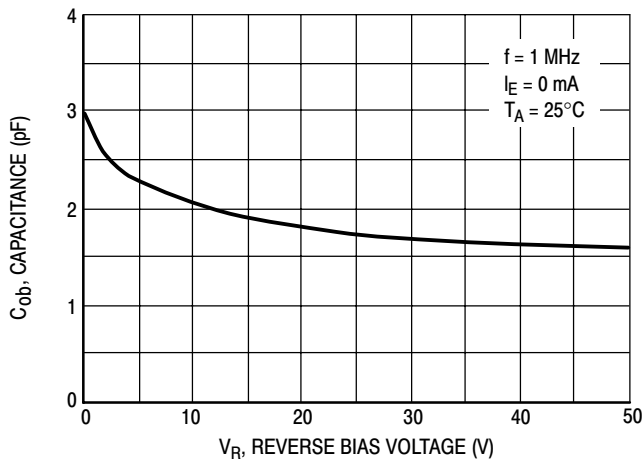


Figure 14. Output Capacitance

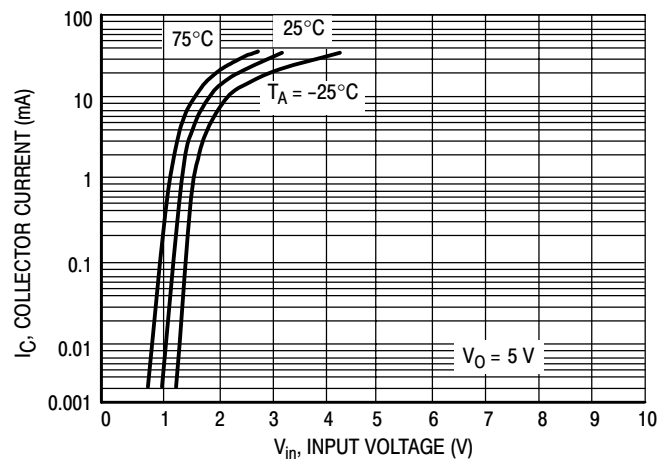


Figure 15. Output Current versus Input Voltage

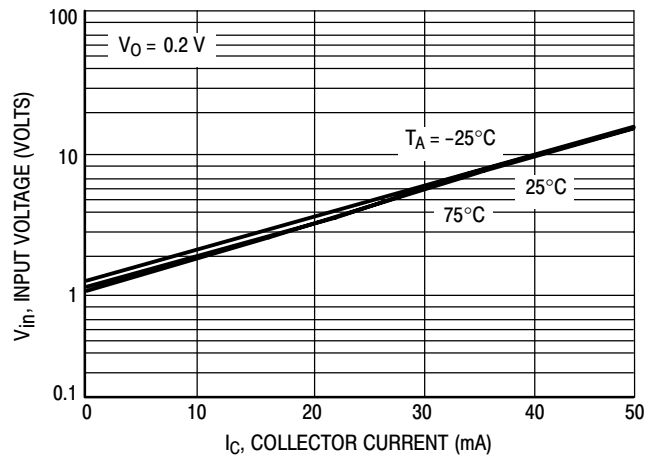


Figure 16. Input Voltage versus Output Current

UMC2NT1, UMC3NT1, UMC5NT1

TYPICAL ELECTRICAL CHARACTERISTICS — UMC3NT1 NPN TRANSISTOR

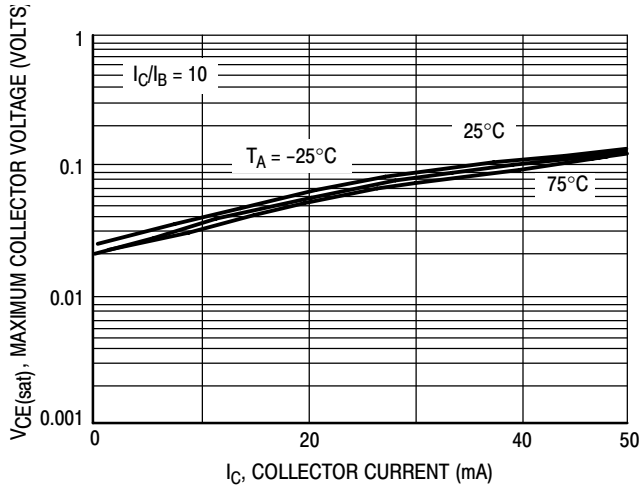


Figure 17. $V_{CE(sat)}$ versus I_C

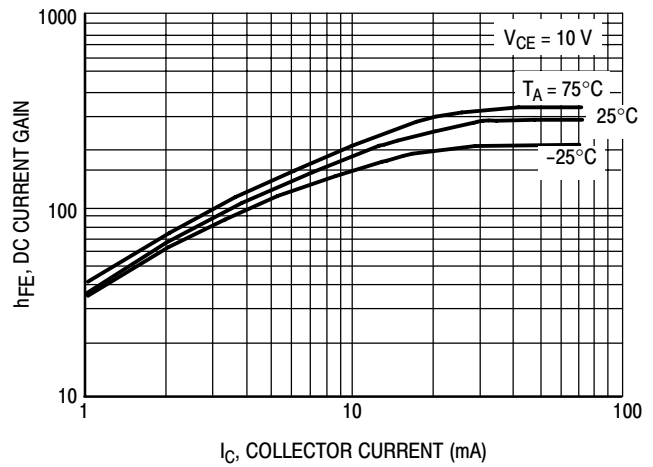


Figure 18. DC Current Gain

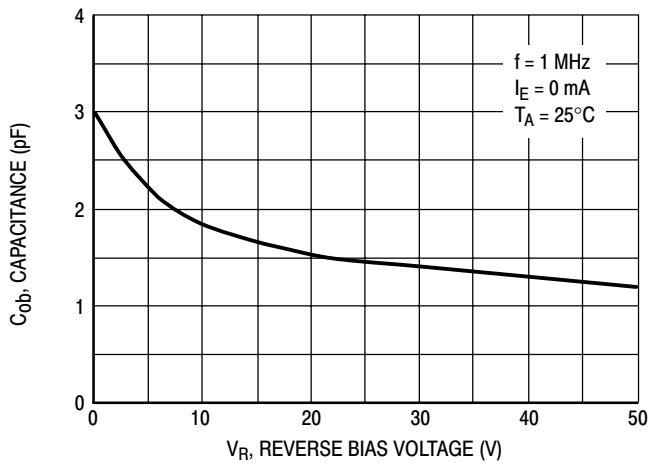


Figure 19. Output Capacitance

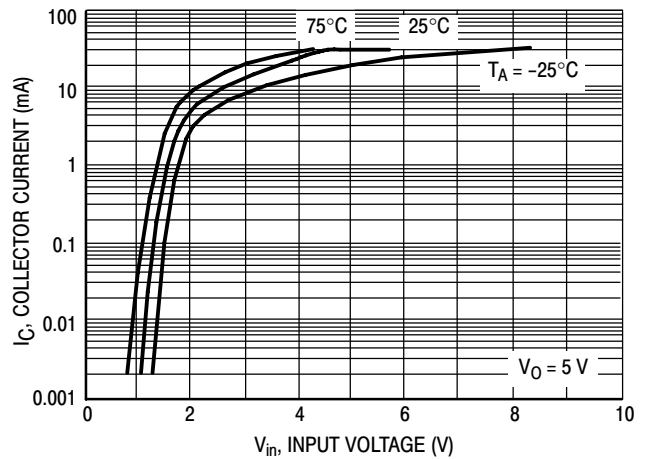


Figure 20. Output Current versus Input Voltage

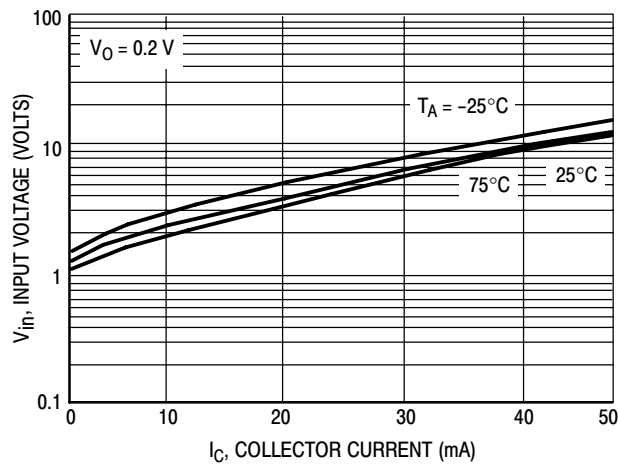


Figure 21. Input Voltage versus Output Current

UMC2NT1, UMC3NT1, UMC5NT1

TYPICAL ELECTRICAL CHARACTERISTICS — UMC5NT1 PNP TRANSISTOR

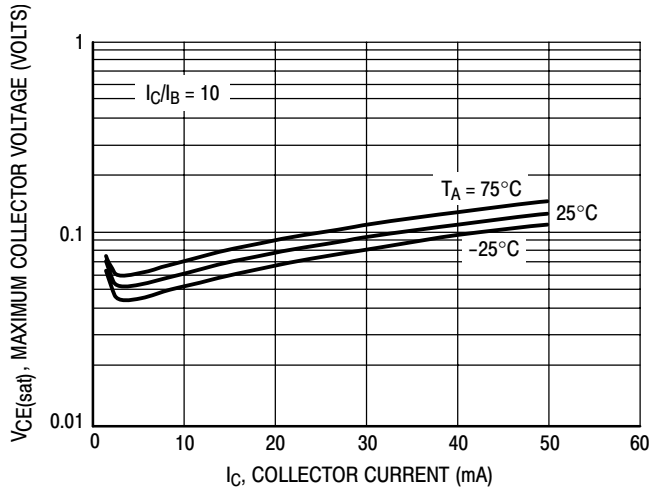


Figure 22. $V_{CE(sat)}$ versus I_C

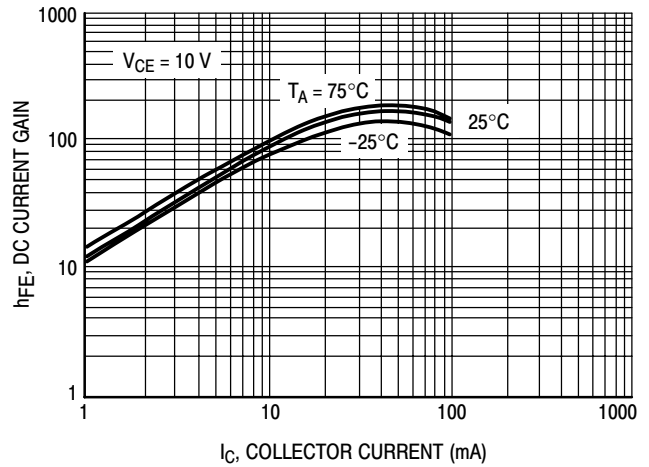


Figure 23. DC Current Gain

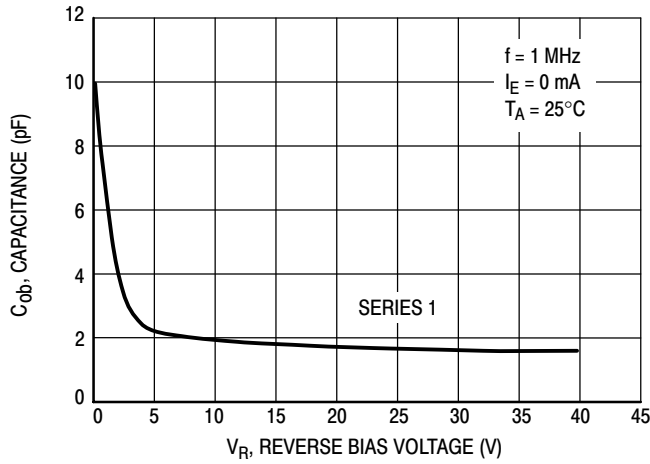


Figure 24. Output Capacitance

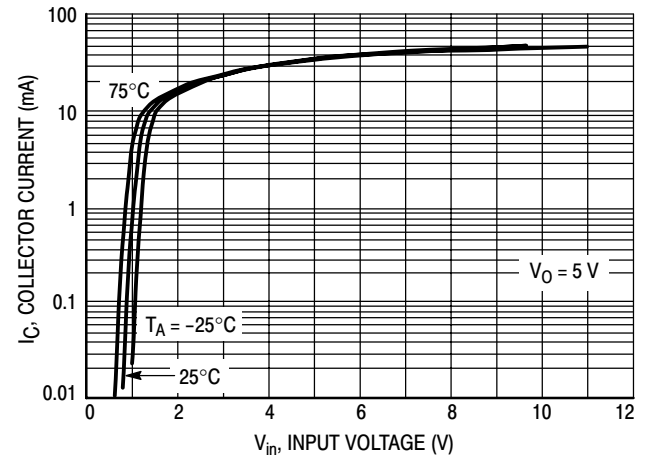


Figure 25. Output Current versus Input Voltage

UMC2NT1, UMC3NT1, UMC5NT1

TYPICAL ELECTRICAL CHARACTERISTICS — UMC5NT1 NPN TRANSISTOR

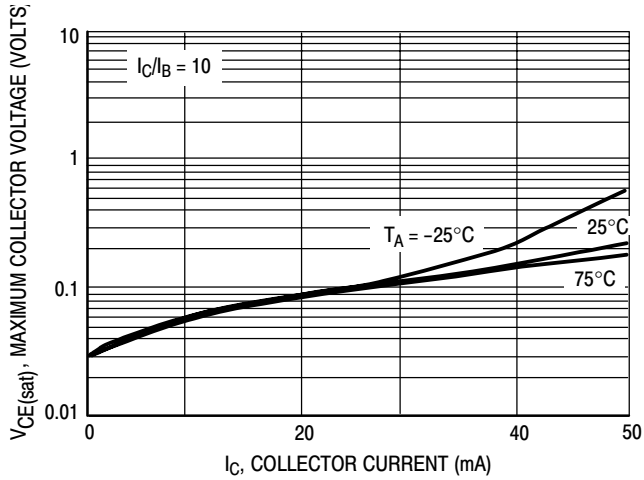


Figure 26. $V_{CE(sat)}$ versus I_C

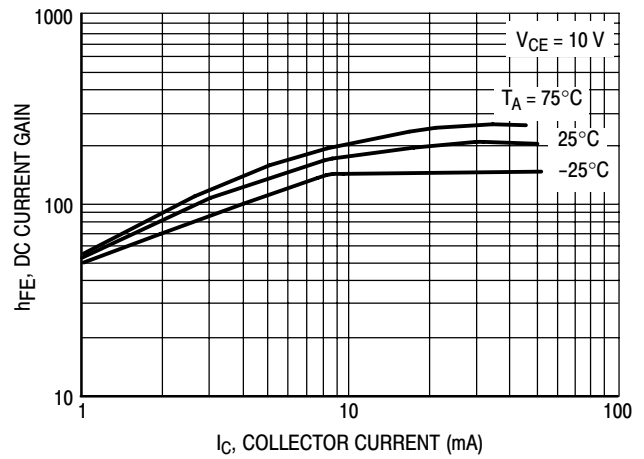


Figure 27. DC Current Gain

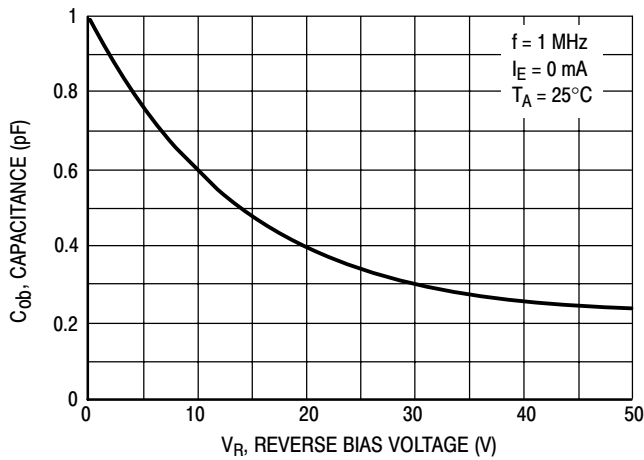


Figure 28. Output Capacitance

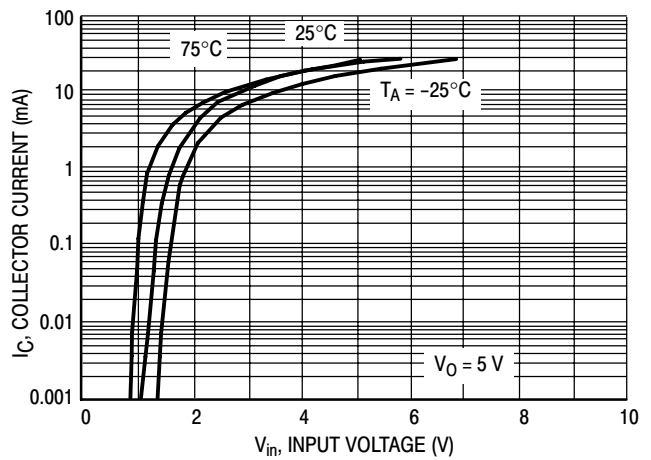


Figure 29. Output Current versus Input Voltage

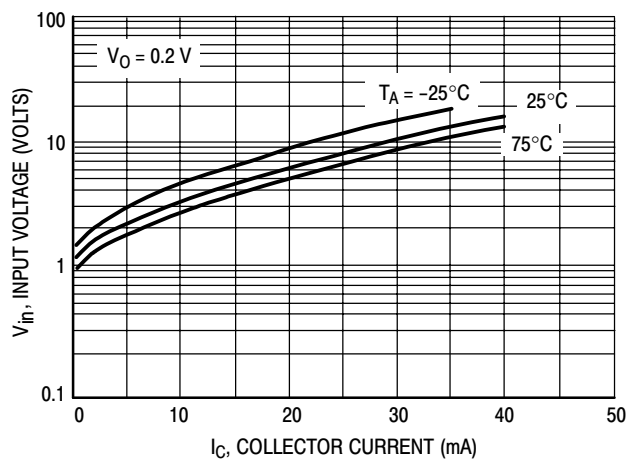
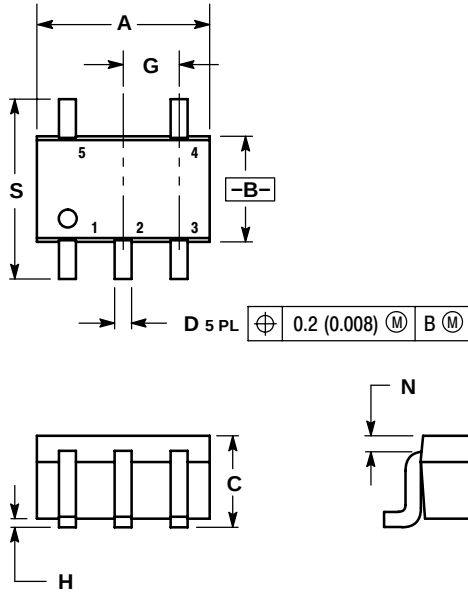


Figure 30. Input Voltage versus Output Current

UMC2NT1, UMC3NT1, UMC5NT1

PACKAGE DIMENSIONS

SC-88A, SOT-353, SC-70
CASE 419A-02
ISSUE J



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

STYLE 6:

- PIN 1. EMITTER 2
2. BASE 2
3. EMITTER 1
4. COLLECTOR
5. COLLECTOR 2/BASE 1

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082-1312 USA
Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada
Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051
Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>

Order Literature: <http://www.onsemi.com/litorder>

For additional information, please contact your local Sales Representative.